

2SC5993

Silicon NPN epitaxial planar type

For power amplification

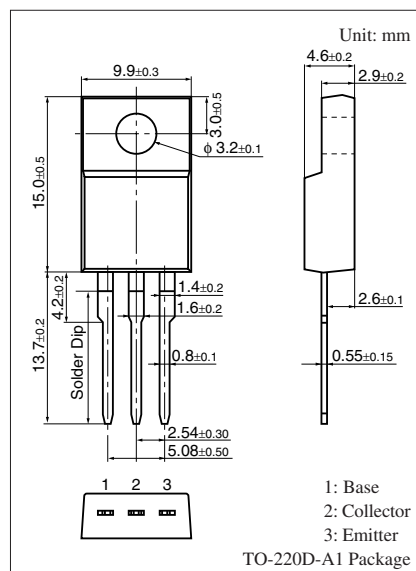
For TV VM circuit

■ Features

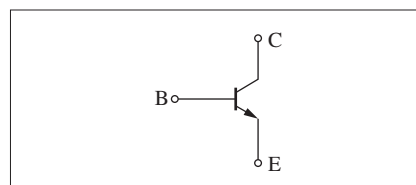
- Satisfactory linearity of forward current transfer ratio h_{FE}
- High transition frequency (f_T)
- Full-pack package which can be installed to the heat sink with one screw.

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	180	V
Collector-emitter voltage (Base open)	V _{CEO}	180	V
Emitter-base voltage (Collector open)	V _{EBO}	6	V
Collector current	I _C	1.5	A
Peak collector current	I _{CP}	3	A
Collector power dissipation	P _C	20	W
		2.0	
T _a = 25°C			
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	−55 to +150	°C



Internal Connection



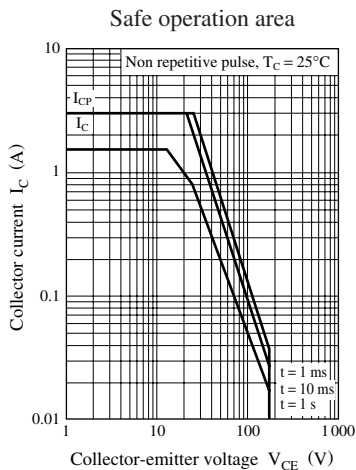
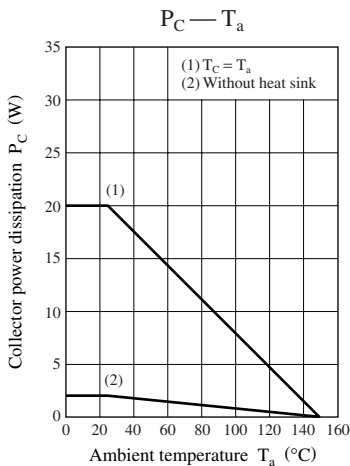
■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 10\text{ mA}, I_B = 0$	180			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 180\text{ V}, I_E = 0$			100	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6\text{ V}, I_C = 0$			100	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ A}$	60		240	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 0.1\text{ A}$			0.5	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.2\text{ A}, f = 10\text{ MHz}$		130		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		10		pF
Turn-on time	t_{on}	$I_C = 0.4\text{ A}, \text{Resistance loaded}$ $I_{B1} = 0.04\text{ A}, I_{B2} = -0.04\text{ A}$ $V_{CC} = 100\text{ V}$		0.1		μs
Storage time	t_{stg}			1.5		μs
Fall time	t_f			0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	P
h_{FE}	60 to 140	120 to 240



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